

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

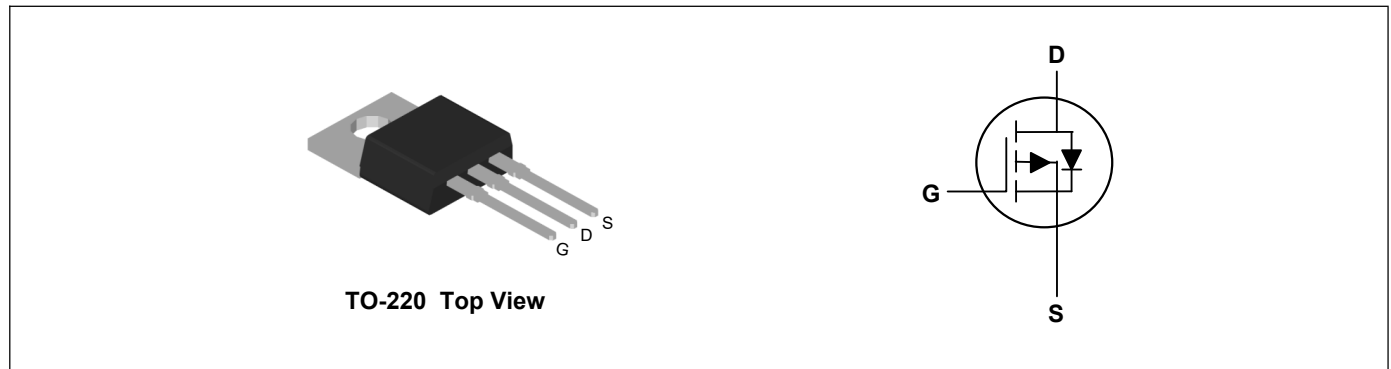
Applications

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

Product Summary



V_{DS}	-100	V
I_D	-35	A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	50	m Ω
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	55	m Ω



Absolute Maximum Ratings($T_C=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ -10V^1$	$I_D@T_C=25^{\circ}C$	-35	A
Continuous Drain Current, $V_{GS} @ -10V^1$	$I_D@T_C=100^{\circ}C$	-23	A
Pulsed Drain Current ²	I_{DM}	-100	A
Single Pulse Avalanche Energy ³	EAS	345	mJ
Avalanche Current	I_{AS}	28	A
Total Power Dissipation ⁴	$P_D@T_C=25^{\circ}C$	104	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62	$^{\circ}C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	1.2	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-100	---	---	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =-10V, I _D =-10A	---	42	50	mΩ
		V _{GS} =-4.5V, I _D =-8A	---	46	55	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.8	-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-50	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =-10V, I _D =-10A	---	32	---	S
Total Gate Charge	Q _g	V _{DS} =-80V, V _{GS} =-10V, I _D =-14A	---	92	---	nC
Gate-Source Charge	Q _{gs}		---	17.5	---	
Gate-Drain Charge	Q _{gd}		---	14	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =-50V, V _{GS} =-10V, R _G =3.3Ω, I _D =-14A	---	20.5	---	ns
Rise Time	T _r		---	32.2	---	
Turn-Off Delay Time	T _{d(off)}		---	123	---	
Fall Time	T _f		---	63.7	---	
Input Capacitance	C _{iss}	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	6516	---	pF
Output Capacitance	C _{oss}		---	223	---	
Reverse Transfer Capacitance	C _{rss}		---	125	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V, Force Current	---	---	-35	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =-14A, di/dt=100A/μs, T _J =25°C	---	31.2	---	nS
Reverse Recovery Charge	Q _{rr}		---	31.97	---	nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.88mH, I_{AS}=-28A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

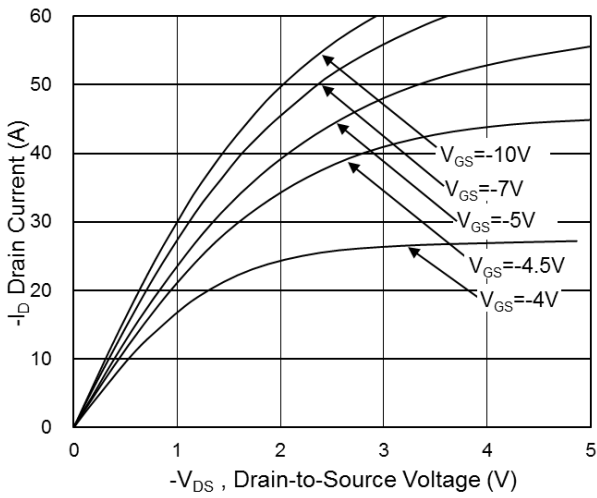


Fig.1 Typical Output Characteristics

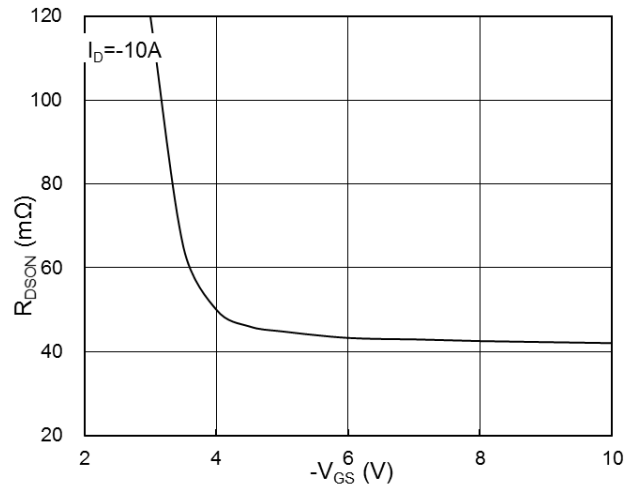


Fig.2 On-Resistance vs. G-S Voltage

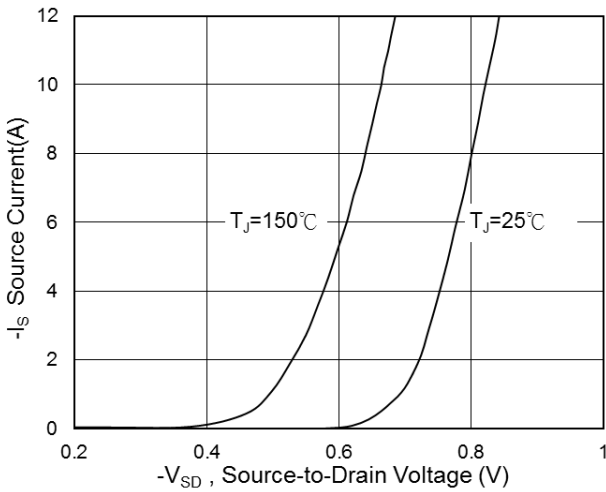


Fig.3 Typical S-D Diode Forward Voltage

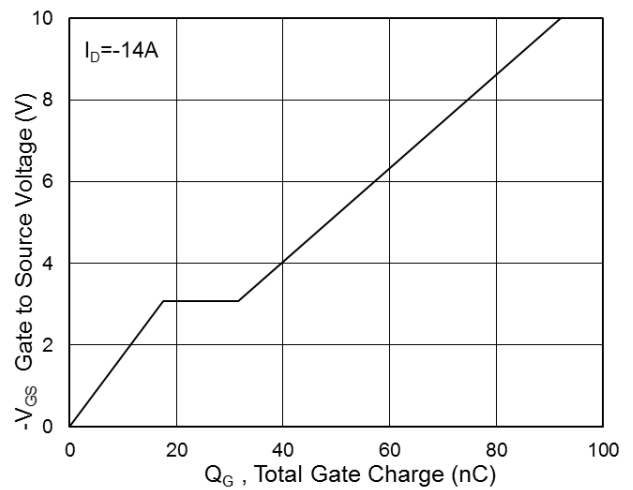


Fig.4 Gate-Charge Characteristics

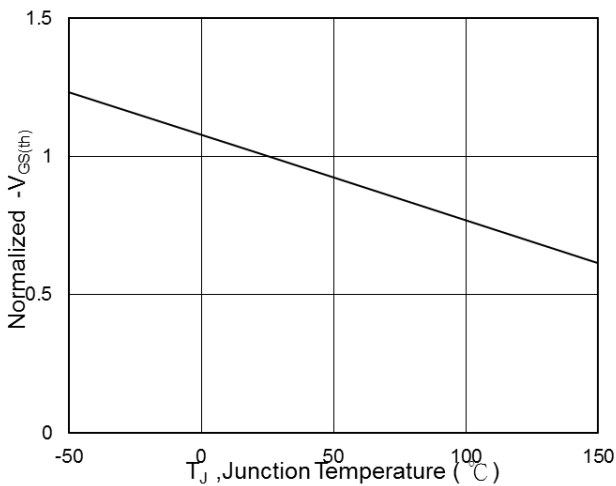


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

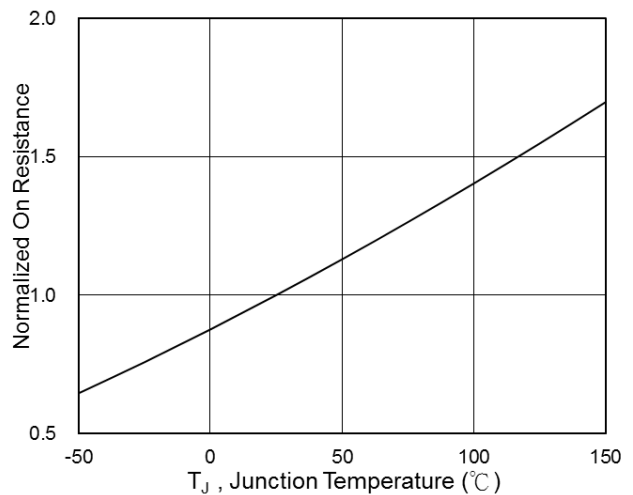


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

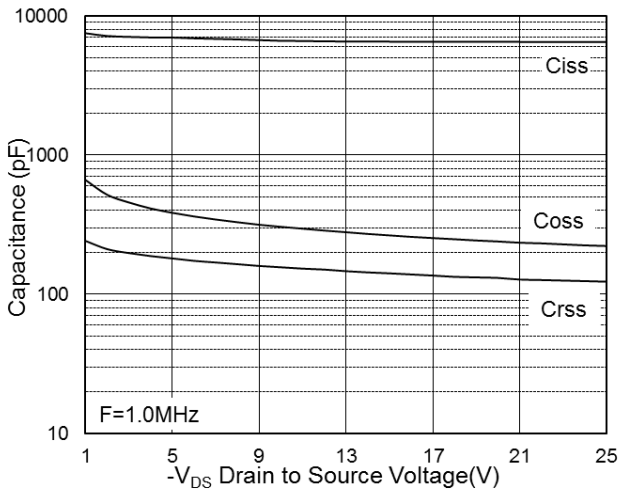


Fig.7 Capacitance

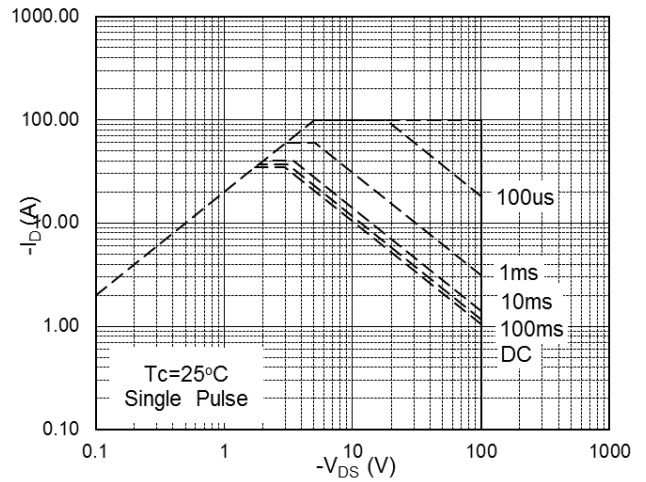


Fig.8 Safe Operating Area

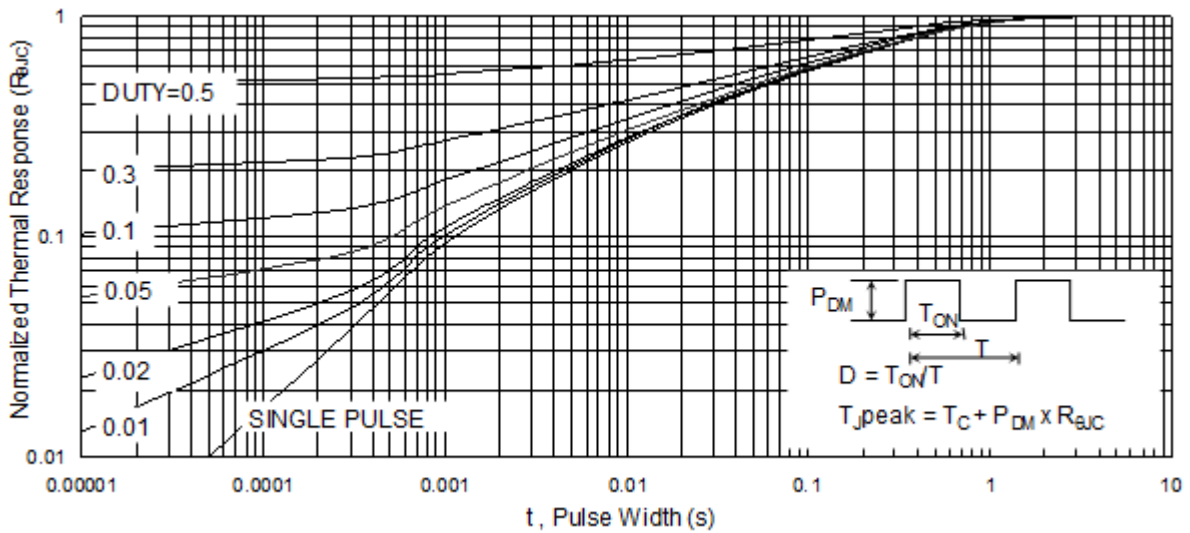


Fig.9 Normalized Maximum Transient Thermal Impedance

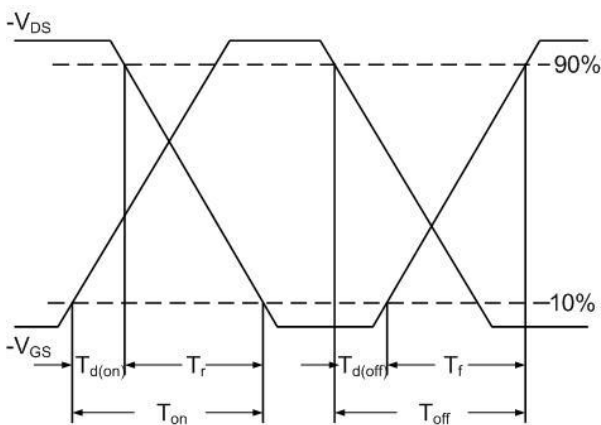


Fig.10 Switching Time Waveform

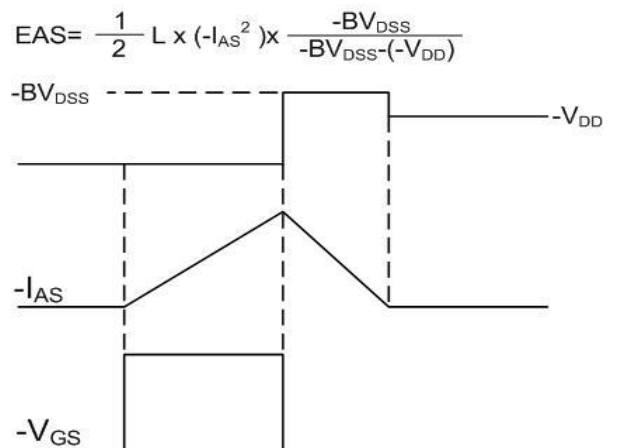
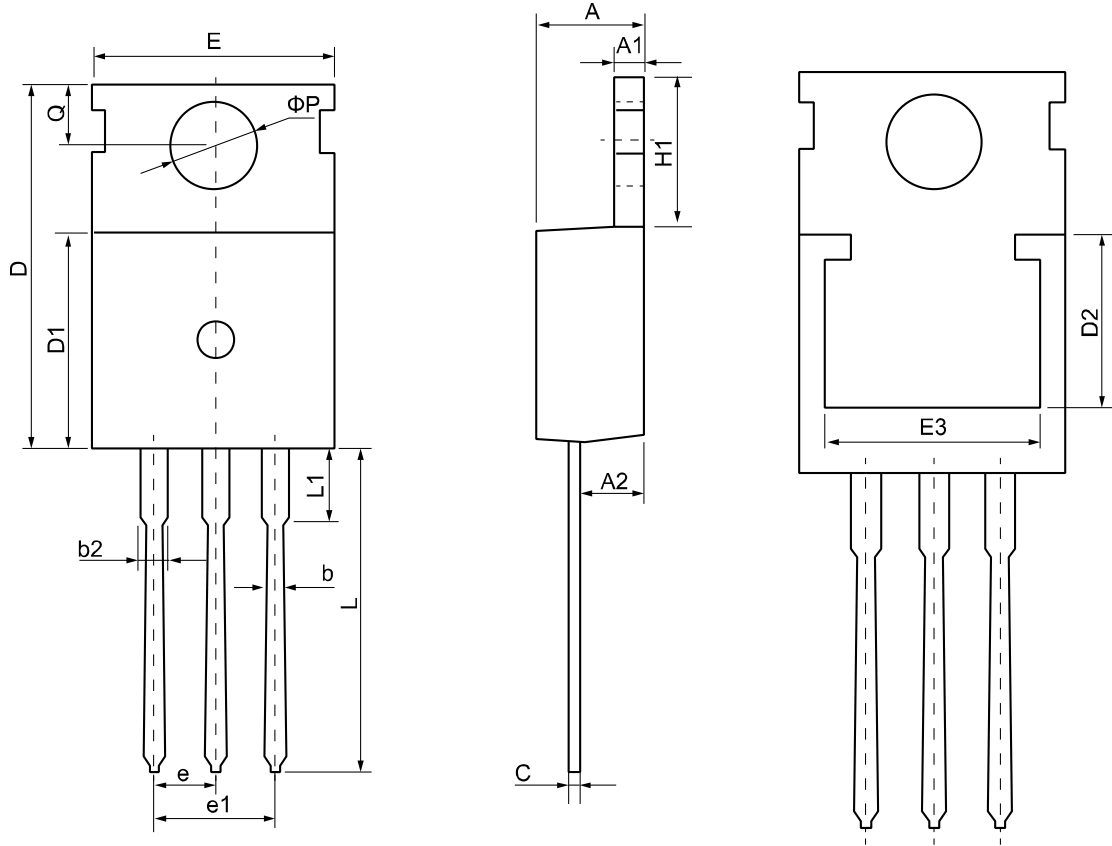


Fig.11 Unclamped Inductive Waveform

TO-220 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.30	4.55	4.75	E	9.65	10.00	10.25
A1	1.15	1.30	1.45	E3	7.00	--	--
A2	2.20	2.40	2.60	e	2.54 BSC		
b	0.70	0.80	0.95	e1	5.08 BSC		
b2	1.17	1.27	1.47	H1	6.30	6.50	6.80
c	0.40	0.50	0.65	L	12.70	13.50	14.10
D	15.30	15.60	15.90	L1	--	3.20	3.95
D1	8.90	9.10	9.35	phi P	3.40	3.60	3.80
D2	5.50	--	--	Q	2.60	2.80	3.00